# NEC

# PNP SILICON POWER TRANSISTOR 2SA1394

**DESCRIPTION** The 2SA1394 is PNP silicon epitaxial transistor designed for

switching regulator, DC-DC converter and high frequency power

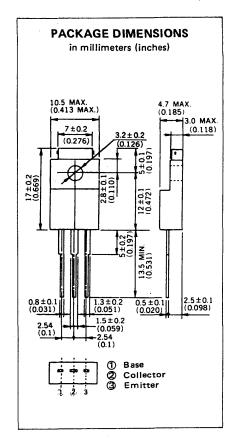
amplifier application.

#### **FEATURES**

- Easy mount by eliminating Insulation Sheet and Bushing.
- Low Collector Saturation Voltage.
- High Switching Speed.
- Complementary to 2SC3566.

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Temperatures							
Storage Temperature							
Junction Temperature 150 °C Maximum							
Maximum Power Dissipation (T <sub>a</sub> = 25 °C)							
Total Power Dissipation 25							
Maximum Voltages and Currents (T <sub>a</sub> = 25 °C)							
V <sub>CBO</sub>	Collector to Base Voltage $-80$	٧					
V <sub>CEO</sub>	Collector to Emitter Voltage $-60$	٧					
$V_{EBO}$	Emitter to Base Voltage $-12$	٧					
I <sub>C(DC)</sub>	Collector Current (DC)5	Α					
(C(pulse)	Collector Current (pulse)*10	Α					
I <sub>B(DC)</sub>	Base Current (DC) −2.5	Α					
* PW ≤ 300 μs, Duty Cycle ≤ 10 %							



# ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
ton	Turn-on Time			0.5	μs	(.	
t <sub>stg</sub>	Storage Time			2.5	μs	$(I_C = -3.0 \text{ A}, I_{B1} = -I_{B2} = -0.3 \text{ A})$ $R_L = 17 \Omega, V_{CC} = -50 \text{ V}$	
tf	Fall Time			0.5	μs	(,, vec = -50 v	
hFE1	DC Current Gain*	40			_	$V_{CE} = -5.0 \text{ V}, I_{C} = -0.3 \text{ A}$	
hFE2	DC Current Gain*	40		200	_	$V_{CE} = -5.0 \text{ V, I}_{C} = -3.0 \text{ A}$	
V <sub>CE(sat)</sub>	Collector Saturation Voltage*			-0.6	V	$I_C = -3.0 \text{ A}, I_B = -0.3 \text{ A}$	
V <sub>BE(sat)</sub>	Base Saturation Voltage*			-1.5	٧	$I_C = -3.0 \text{ A}, I_B = -0.3 \text{ A}$	
VCEO(SUS)	Collector to Emitter Sustaining Voltage	-60			V	$I_C = -3.0 \text{ A}, I_B = -0.3 \text{ A}, L = 1 \text{ mH}$	
V <sub>CEX</sub> (SUS)1	Collector to Emitter Sustaining Voltage	-60			V	$I_C = -3.0 \text{ A}, I_{B1} = -I_{B2} = -0.3 \text{ A},$ L = 180 $\mu$ H, Clamped	
V <sub>CEX</sub> (SUS)2	Collector to Emitter Sustaining Voltage	60			V	$I_C = -6.0 \text{ A}, I_{B1} = -0.6 \text{ A},$ $-I_{B2} = 0.3 \text{ A}, L = 180 \mu\text{H}, Clamped}$	
ICBO	Collector Cutoff Current			-10	μΑ	$V_{CB} = -60 \text{ V}, I_E = 0$	
CER	Collector Cutoff Current			-1.0	mA	$V_{CE} = -60 \text{ V}, R_{BE} = 51 \Omega, T_a = 125 ^{\circ}\text{C}$	
ICEX1	Collector Cutoff Current			-10	μΑ	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V}$	
CEX2	Collector Cutoff Current			-1.0	mA	$V_{CE} = -60 \text{ V}, V_{BE(OFF)} = 1.5 \text{ V},$ $T_a = 125 ^{\circ}\text{C}$	
IEBO	Emitter Cutoff Current			-10	μΑ	$V_{EB} = -10 \text{ V, I}_{C} = 0$	

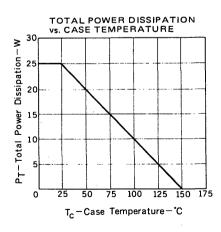
\* PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

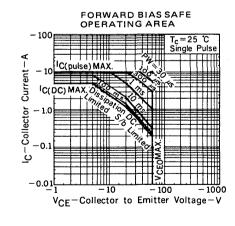
## Classification of hFE2

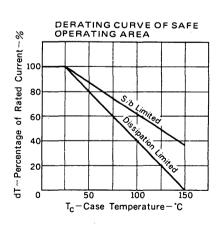
Rank	М	L	к
Range	40 to 80	60 to 120	100 to 200

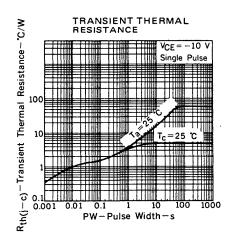
Test Conditions:  $V_{CE} = -5.0 \text{ V}$ ,  $I_{C} = -3.0 \text{ A}$ 

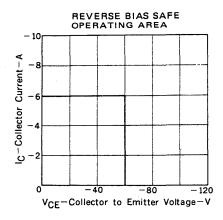
## TYPICAL CHARACTERISTICS (Ta = 25 °C)

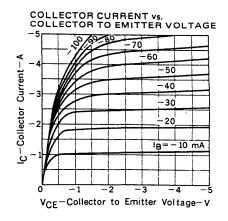


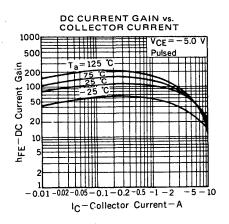


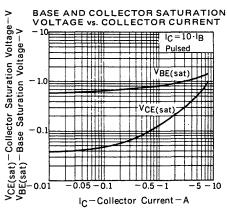


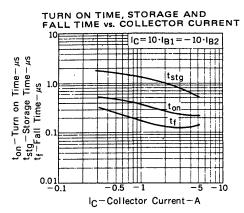












SWITCHING TIME  $(t_{on}, t_{stg}, t_f)$  TEST CIRCUIT

